Broadband power LDMOS transistor

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AMPLEON

Product data sheet

1. Product profile

1.1 General description

A 100 W LDMOS RF power push-pull transistor for broadcast transmitter and industrial applications. The transistor is suitable for the frequency range HF to 1400 MHz. The excellent ruggedness and broadband performance of this device makes it ideal for digital applications.

Table 1. Typical performance

RF performance at $T_h = 25$ °C in a common source test circuit.

| Mode of operation | f (MHz) | V _{DS} | P _L (W) | P _{L(PEP)} (W) | G _p | η _D (%) | IMD (dBc) |
|-------------------|------------|-----------------|-----------------------|-------------------------|----------------|-----------------------|--------------|
| CW, class-AB | 1300 | 32 | 100 | - | 18 | 56 | - |
| 2-tone, class-AB | 1300 | 32 | - | 100 | 18 | 45 | -32 |

1.2 Features

- CW performance at 1300 MHz, a drain-source voltage V_{DS} of 32 V and a quiescent drain current I_{Dq} = 0.9 A for total device:
 - ◆ Average output power = 100 W
 - ◆ Power gain = 18 dB
 - ◆ Drain efficiency = 56 %
- 2-tone performance at 1300 MHz, a drain-source voltage V_{DS} of 32 V and a quiescent drain current I_{Dq} = 0.9 A for total device:
 - Peak envelope load power = 100 W
 - ◆ Power gain = 18 dB
 - ◆ Drain efficiency = 45 %
 - ◆ Intermodulation distortion = -32 dBc
- Integrated ESD protection
- Excellent ruggedness
- High power gain
- High efficiency
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

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1.3 Applications

- Communication transmitter applications in the HF to 1400 MHz frequency range
- Industrial applications in the HF to 1400 MHz frequency range

2. Pinning information

Table 2. Pinning

| Table 2. | Filling | | |
|----------|-------------|--------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1 | drain 1 | | , |
| 2 | drain 2 | | 1 |
| 3 | gate 1 | | 3 |
| 4 | gate2 | 3 4 | 5 |
| 5 | source | <u>(1)</u> | 2 sym117 |

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BLF645 | - | flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads | SOT540A |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|------------|-----------------|------|------|
| V_{DS} | drain-source voltage | | - | 65 | V |
| V_{GS} | gate-source voltage | | -0.5 | +11 | V |
| I _D | drain current | | - | 32 | Α |
| T _{stg} | storage temperature | | - 65 | +150 | °C |
| T _j | junction temperature | | - | 200 | °C |

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Typ Unit |
|---------------|--|---|--------------|
| $R_{th(j-c)}$ | thermal resistance from junction to case | $T_{case} = 80 ^{\circ}C; P_{L} = 100 W$ | [1] 0.67 K/W |

^[1] R_{th(i-c)} is measured under RF conditions.

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Characteristics 6.

Table 6. Characteristics per section

 $T_i = 25$ °C per section; unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|----------------------------------|---|-----|-----|-----|------|
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $V_{GS} = 0 \text{ V}; I_D = 0.9 \text{ mA}$ | 65 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | V_{DS} = 32 V; I_{D} = 90 mA | 1.4 | 1.9 | 2.4 | V |
| V_{GSq} | gate-source quiescent voltage | V_{DS} = 32 V; I_{Dq} = 450 mA | 1.5 | 2.0 | 2.5 | V |
| I_{DSS} | drain leakage current | $V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V}$ | - | - | 1.4 | μΑ |
| I _{DSX} | drain cut-off current | $V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$ | - | 14 | - | Α |
| I_{GSS} | gate leakage current | V_{GS} = ±10 V; V_{DS} = 0 V | - | - | 120 | nA |
| g _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 4.5 A | - | 6.4 | - | S |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 3.15 A$ | - | 220 | - | mΩ |
| C _{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V};$ f = 1 MHz | - | 69 | - | pF |
| C _{oss} | output capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V};$ f = 1 MHz | - | 25 | - | pF |
| C _{rs} | feedback capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V};$ f = 1 MHz | - | 1.2 | - | pF |

Application information

RF performance in a common-source class-AB circuit $T_h = 25$ °C; $I_{Dq} = 0.9$ A for total device.

| Mode of operation | f | V _{DS} | P _L | G _p | η _D |
|-------------------|-------|-----------------|----------------|----------------|----------------|
| | (MHz) | (V) | (W) | (dB) | (%) |
| CW, class-AB | 1300 | 32 | 100 | > 16.5 | > 53 |

7.1 Ruggedness in class-AB operation

The BLF645 is capable of withstanding a load mismatch corresponding to VSWR = 10:1 through all phases under the following conditions: V_{DS} = 32 V; f = 1300 MHz at rated load power.

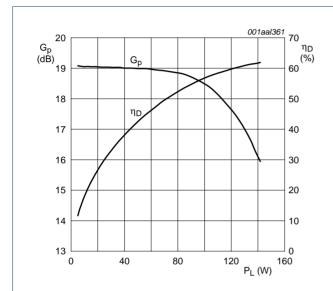
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8. Test information

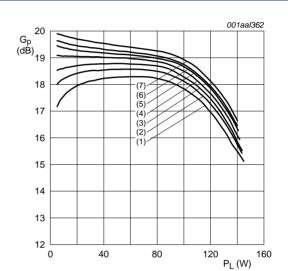
8.1 RF performance

The following figures are measured in a class-AB production test circuit.

8.1.1 1-Tone CW



 V_{DS} = 32 V; I_{Dq} = 900 mA (for total device); f = 1300 MHz.



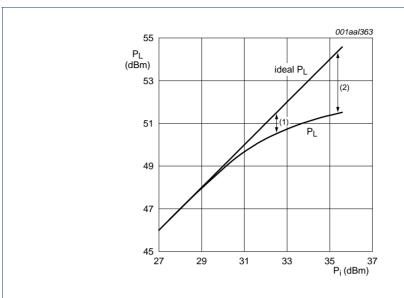
 $V_{DS} = 32 \text{ V}$; f = 1300 MHz.

- (1) I_{Dq} = 200 mA (for total device).
- (2) $I_{Dq} = 400 \text{ mA}$ (for total device).
- (3) I_{Dq} = 600 mA (for total device).
- (4) $I_{Dq} = 900 \text{ mA}$ (for total device).
- (5) $I_{Dq} = 1200 \text{ mA}$ (for total device).
- (6) $I_{Dq} = 1400 \text{ mA}$ (for total device).
- (7) I_{Dq} = 1800 mA (for total device).

Fig 1. Power gain and drain efficiency as function of load power; typical values

Fig 2. Power gain as a function of load power; typical values

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 V_{DS} = 32 V; I_{Dq} = 900 mA (for total device); f = 1300 MHz.

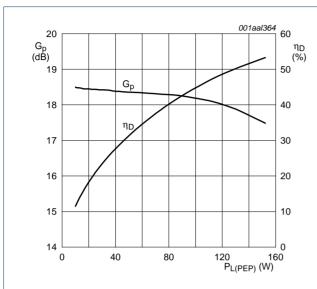
- (1) $P_{L(1dB)} = 50.5 \text{ dBm } (112 \text{ W}).$
- (2) $P_{L(3dB)} = 51.5 \text{ dBm } (141 \text{ W}).$

Fig 3. Load power as function of input power; typical values

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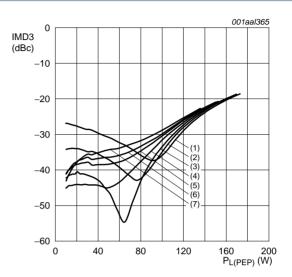
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8.1.2 2-Tone CW



 V_{DS} = 32 V; I_{Dq} = 900 mA (for total device); f = 1300 MHz; carrier spacing = 100 kHz.

Fig 4. Power gain and drain efficiency as function of peak envelope load power; typical values



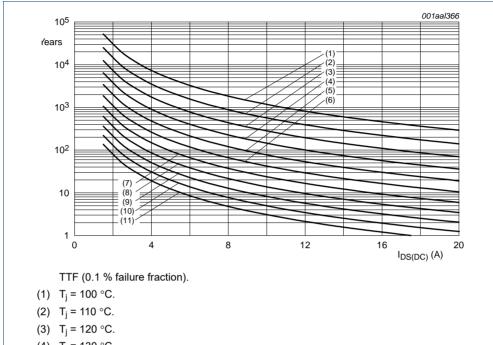
 V_{DS} = 32 V; f = 1300 MHz; carrier spacing = 100 kHz.

- (1) I_{Dq} = 200 mA (for total device).
- (2) I_{Dq} = 400 mA (for total device).
- (3) I_{Dq} = 600 mA (for total device).
- (4) $I_{Dq} = 900 \text{ mA}$ (for total device).
- (5) $I_{Dq} = 1200 \text{ mA (for total device)}$.
- (6) $I_{Dq} = 1400 \text{ mA (for total device)}$
- (7) $I_{Dq} = 1800 \text{ mA}$ (for total device).

Fig 5. Third order intermodulation distortion as a function of peak envelope load power; typical values

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8.2 Reliability

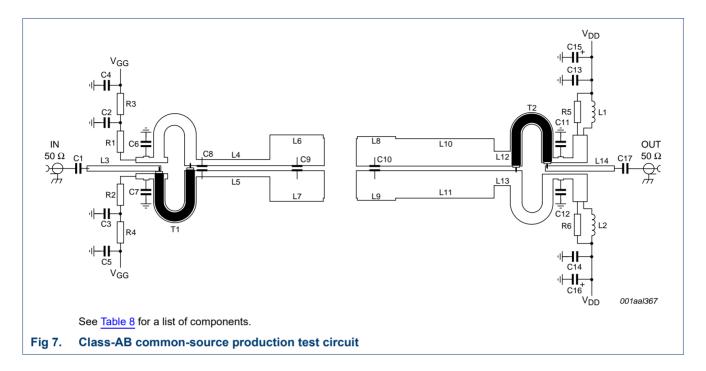


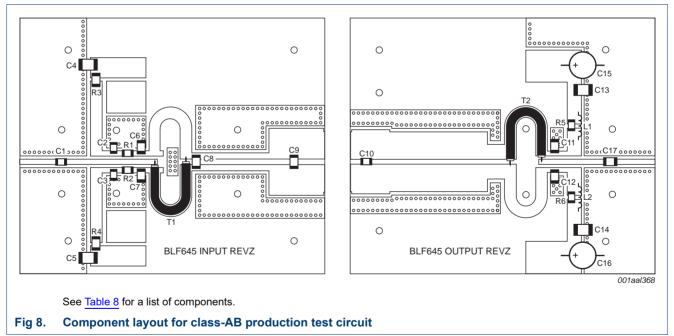
- (4) $T_i = 130 \, ^{\circ}C$.
- (5) $T_j = 140 \, ^{\circ}\text{C}$.
- (6) $T_i = 150 \, ^{\circ}C$.
- (7) $T_j = 160 \, ^{\circ}C$.
- (8) $T_j = 170 \, ^{\circ}\text{C}$.
- (9) $T_j = 180 \, ^{\circ}C$.
- (10) $T_i = 190 \, ^{\circ}C$.
- (11) $T_i = 200 \, ^{\circ}C$.

Fig 6. BLF645 electromigration ($I_{DS(DC)}$, total device)

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8.3 Test circuit





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Table 8. List of components

For test circuit, see Figure 7 and Figure 8.

| Component | Description | Value | | Remarks |
|--------------------------|--------------------------------------|-------------------------------------|-----|---|
| C1 | multilayer ceramic chip capacitor | 47 pF | [1] | |
| C6, C7, C11, C12, C17 | multilayer ceramic chip capacitor | 27 pF | [2] | |
| C2, C3 | multilayer ceramic chip capacitor | 100 nF | | Murata X7R or equivalent |
| C4, C5, C13, C14 | multilayer ceramic chip capacitor | 4.7 μF | | TDK C4532X7R1E475MT020U or capacitor of same quality. |
| C8 | multilayer ceramic chip capacitor | 1.5 pF | [2] | |
| C9 | multilayer ceramic chip capacitor | 3.3 pF | [2] | |
| C10 | multilayer ceramic chip capacitor | 6.2 pF | [3] | |
| C15, C16 | electrolytic capacitor | 220 μF | | TDK C4532X7R1E475MT020U or capacitor of same quality. |
| L1, L2 | 4 turns, 0.8 mm enameled copper wire | D = 3.5 mm; length = 4 mm | | |
| L3 | microstrip | - | [4] | (W × L) 1.67 mm × 19.17 mm |
| L4, L5 | microstrip | - | [4] | (W × L) 1.9 mm × 23.7 mm |
| L6, L7 | microstrip | - | [4] | (W × L) 9.6 mm × 17.3 mm |
| L8, L9 | microstrip | - | [4] | (W × L) 9 mm 12 mm |
| L10, L11 | microstrip | - | [4] | (W \times L) 8.5 mm \times 31.0 mm |
| L12, L13 | microstrip | - | [4] | (W \times L) 4.52 mm \times 5.0 mm |
| L14 | microstrip | - | [4] | (W × L) 1.67 mm × 21.67 mm |
| R1, R2 | SMD resistor | 11 Ω | | 1206 |
| R3, R4 | SMD resistor | 1 kΩ | | 1206 |
| R5, R6 | SMD resistor | 12 Ω | | 1206 |
| T1, T2 | semi rigid coax | $Z = 50 \Omega$; length = 34 mm | | |

^[1] American technical ceramics type 100A or capacitor of same quality.

^[2] American technical ceramics type 100B or capacitor of same quality.

^[3] American technical ceramics type 180R or capacitor of same quality.

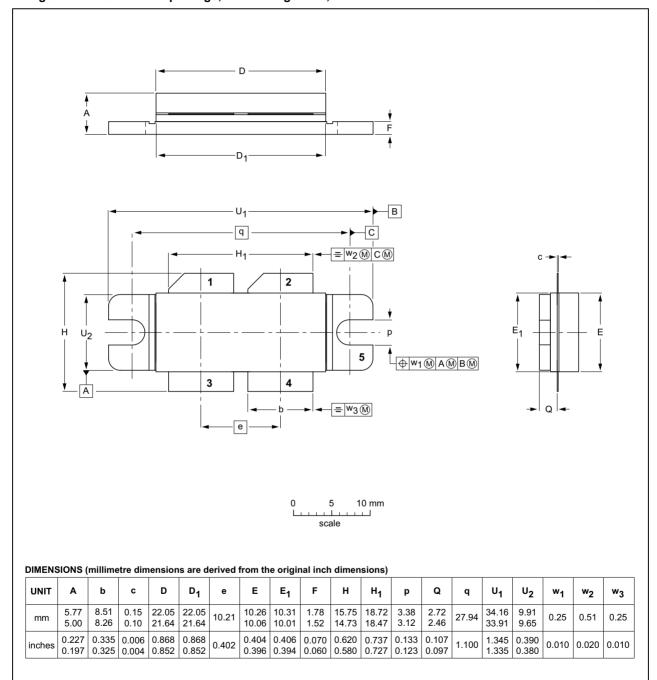
^[4] Printed-Circuit Board (PCB): Taconic RF35; ε_r = 3.5 F/m; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35 μ m.

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9. Package outline

Flanged balanced ceramic package; 2 mounting holes; 4 leads

SOT540A



| OUTLINE | | REFER | RENCES | EUROPEAN ISSUE DATE | | |
|---------|-----|-------|--------|---------------------|----------------------------------|--|
| VERSION | IEC | JEDEC | EIAJ | PROJECTION | ISSUE DATE | |
| SOT540A | | | | | -99-12-28 12-05-02 | |

Fig 9. Package outline SOT540A

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10. Abbreviations

Table 9. Abbreviations

| Acronym | Description |
|---------|---|
| CW | Continuous Waveform |
| DC | Direct Current |
| D-MOS | Diffusion Metal-Oxide Semiconductor |
| ESD | ElectroStatic Discharge |
| HF | High Frequency |
| LDMOS | Laterally Diffused Metal Oxide Semiconductor |
| LDMOST | Laterally Diffused Metal-Oxide Semiconductor Transistor |
| RF | Radio Frequency |
| SMD | Surface-Mount Device |
| VSWR | Voltage Standing-Wave Ratio |

11. Revision history

Table 10. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--|--------------------|---------------|------------|
| BLF645#2 | 20150901 | Product data sheet | - | BLF645_1 |
| Modifications: | The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. | | | |
| | Legal texts have been adapted to the new company name where appropriate. | | | |
| BLF645_1 | 20100127 | Product data sheet | - | - |

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|--------------------------------|-------------------|---|--|
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